WEST Search History for Application 10080958

Creation Date: 2008032411:05

Query	DB	Op.	Plur.	Thes.	Date
memory cell	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell) and float$ near3 (bitline or bit line)	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell and float$ near3 (bitline or bit line)) and (wordline or word line)	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell and float$ near3 (bitline or bit line) and (wordline or word line)) and threshold	PGPB, USPT	ADJ	YES	.	03-24-2008
(memory cell and float$ near3 (bitline or bit line) and (wordline or word line)) and threshold voltage	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell and float$ near3 (bitline or bit line) and (wordline or word line) and threshold voltage) and sens$	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell and float$ near3 (bitline or bit line) and (wordline or word line) and threshold voltage and sens$) and first voltage near3 minus near3 threshold	PGPB, USPT	ADJ	YES		03-24-2008
(memory cell and float$ near3 (bitline or bit line) and (wordline or word line) and threshold voltage and sens$) and select gate	PGPB, USPT	ADJ	YES		03-24-2008